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Kind regards,

Team Nexperia

PEMD16; PUMD16

NPN/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

Rev. 3 — 28 June 2011

Product data sheet

1. Product profile

1.1 General description

NPN/PNP resistor-equipped transistors.

Table 1. Product overview

Type number Package			PNP/PNP	NPN/NPN	
	NXP	JEITA	complement	complement	
PEMD16	SOT666	-	PEMB16	PEMH16	
PUMD16	SOT363	SC-88	PUMB16	PUMH16	

1.2 Features and benefits

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	



2. Pinning information

Table 3. Pinning

Table 5.	· ····································		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1 R1 2 3 006aaa143

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PEMD16	-	plastic surface-mounted package; 6 leads	SOT666
PUMD16	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMD16	5H
PUMD16	D1*

^{[1] * =} placeholder for manufacturing site code

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor v	vith negative polari	ity		
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
VI	input voltage TR1				
	positive		-	+40	V
	negative		-	-7	V
	input voltage TR2				
	positive		-	+7	V
	negative		-	-40	V
Io	output current		-	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		[1][2] -	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1][2]	300	mW

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7. Thermal characteristics

merma enaracteristics					
Parameter	Conditions	Min	Тур	Max	Unit
tor					
thermal resistance from junction to ambient	in free air				
SOT363		<u>[1]</u> -	-	625	K/W
SOT666		[1][2] _	-	625	K/W
thermal resistance from junction to ambient	in free air				
SOT363		<u>[1]</u> -	-	416	K/W
SOT666		[1][2] _	-	416	K/W
	thermal resistance from junction to ambient SOT363 SOT666 thermal resistance from junction to ambient SOT363	Parameter Conditions tor thermal resistance from junction to ambient SOT363 SOT666 thermal resistance from junction to ambient SOT363	Parameter Conditions Min tor thermal resistance from junction to ambient SOT363 [1] - SOT666 [1][2] - thermal resistance from junction to ambient SOT363 in free air junction to ambient SOT363 [1] -	Parameter Conditions Min Typ tor thermal resistance from junction to ambient SOT363 [1] SOT666 [1][2] thermal resistance from junction to ambient SOT363 in free air	thermal resistance from junction to ambient SOT363 SOT666 SOT666 SOT666 In free air junction to ambient in free air junction to ambient SOT363 SOT363 In free air junction to ambient SOT363

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

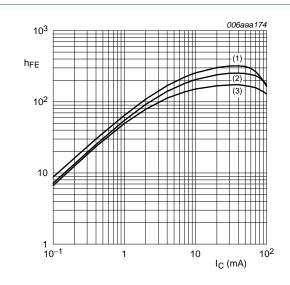
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor; for the PNP tran	nsistor with negative polarit	t y			
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V; } I_{B} = 0 \text{ A;}$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	50	μА
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	120	μА
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	80	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	0.8	0.5	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 2 \text{ mA}$	2	1.1	-	V
R1	bias resistor 1 (input)		15.4	22	28.6	$k\Omega$
R2/R1	bias resistor ratio		1.7	2.1	2.6	
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$				
	TR1 (NPN)		-	-	2.5	pF
	TR2 (PNP)		-	-	3	pF

^[2] Reflow soldering is the only recommended soldering method.



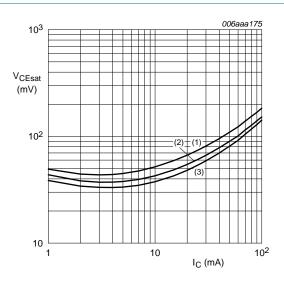
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. TR1 (NPN): DC current gain as a function of collector current; typical values



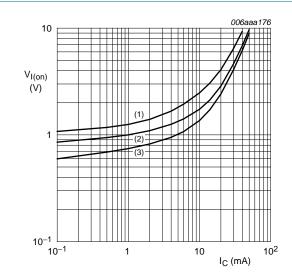
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



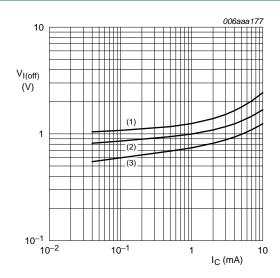
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 3. TR1 (NPN): On-state input voltage as a function of collector current; typical values



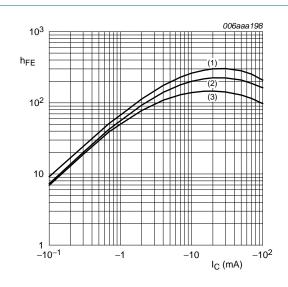
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 4. TR1 (NPN): Off-state input voltage as a function of collector current; typical values



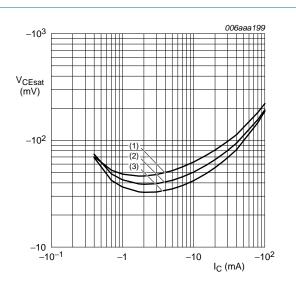
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. TR2 (PNP): DC current gain as a function of collector current; typical values



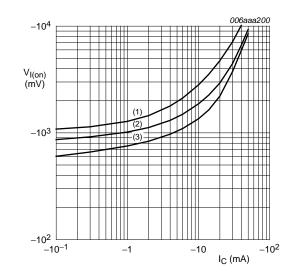
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 6. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



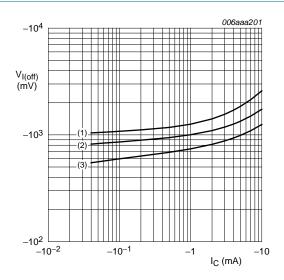
$$V_{CE} = -0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. TR2 (PNP): On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

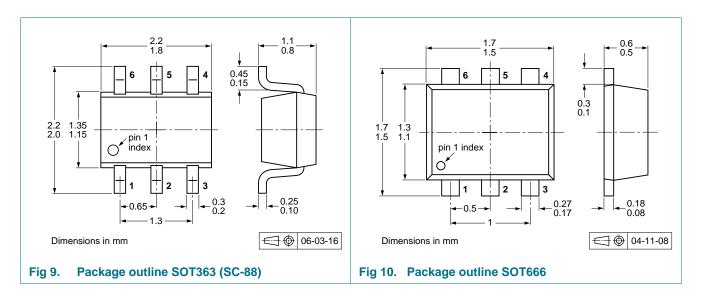
(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 8. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

8. Package outline



9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description		Packing	g quantit	y
				3000	4000	10000
PEMD16	SOT666	4 mm pitch, 8 mm tape and reel		-	-115	-
PUMD16	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-165

^[1] For further information and the availability of packing methods, see Section 12.

^[2] T1: normal taping

^[3] T2: reverse taping

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMD16_PUMD16 v.3	20110628	Product data sheet	-	PEMD16_PUMD16 v.2
Modifications:		nis document has been red XP Semiconductor.	lesigned to comply wi	th the new identity
	 Legal texts hav 	e been adapted to the new	company name whe	re appropriate.
	 Figure 9 "Packa" 	age outline SOT363 (SC-88	8)" is updated.	
	Section 11 "Leg	<u>jal information"</u> is updated.		
PEMD16_PUMD16 v.2	20050607	Product data sheet	-	PUMD16 v.1
PUMD16 v.1	20031022	Product specification	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PEMD16_PUMD16

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PEMD16; PUMD16

NPN/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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